



NASA Electronic Parts and Packaging (NEPP) Program



# Surge Current Testing and Derating for Solid Tantalum Capacitors

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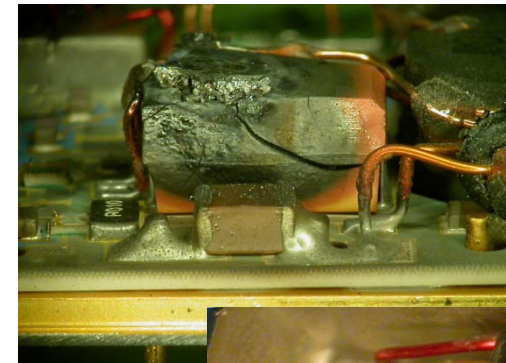
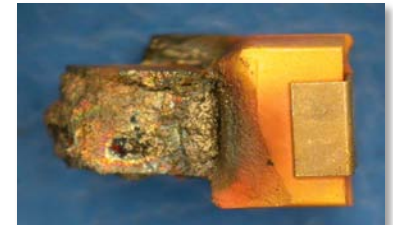
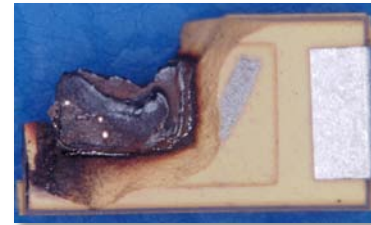
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# Outline

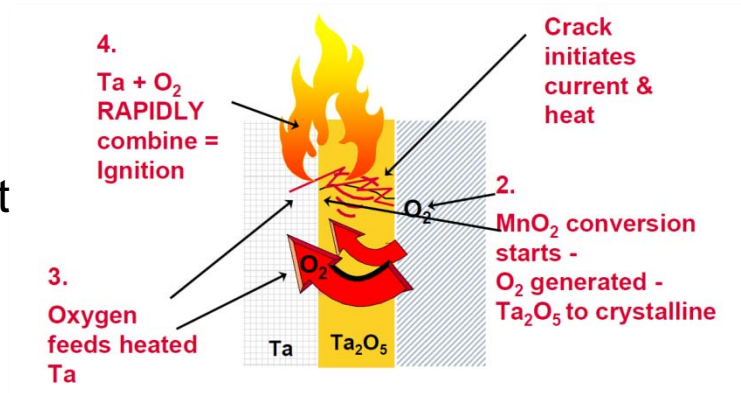
*Do we need limiting resistors in series with tantalum capacitors?*

- ❑ Surge current testing (SCT).
  - Mechanism of failures.
  - History of current derating.
- ❑ MIL-PRF-55635 requirements.
- ❑ Specifics of SCT.
  - Effective resistance of the circuit,  $R_{\text{eff}}$ .
  - Correlation between  $R_{\text{eff}}$  and equivalent series resistance (ESR).
  - Effect of ESR on VBR.
- ❑ Specified and real ESR values.
- ❑ Derating of surge currents.
- ❑ Conclusion.

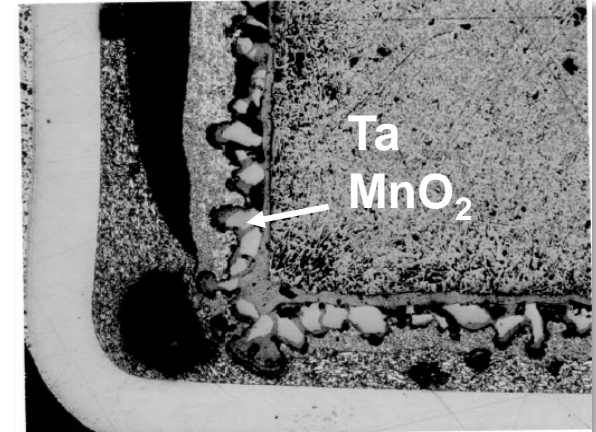


# Mechanisms of Surge Current Failures

- ❑ Sustained scintillation breakdown.  
If current is not limited, self-healing does not have time to develop.
  - ❑ Electrical oscillations in circuits with high inductance.
  - ❑ Local overheating of the cathode.
  - ❑ Mechanical damage to tantalum pentoxide dielectric caused by the impact of  $MnO_2$  crystals.
  - ❑ Stress-induced-generation of electron traps caused by electromagnetic forces developed by high currents.
- ✓ All models require high currents that correspond to high rates of voltage increase.



Ignition due to exothermic reaction in tantalum capacitors. Prymak 2006.

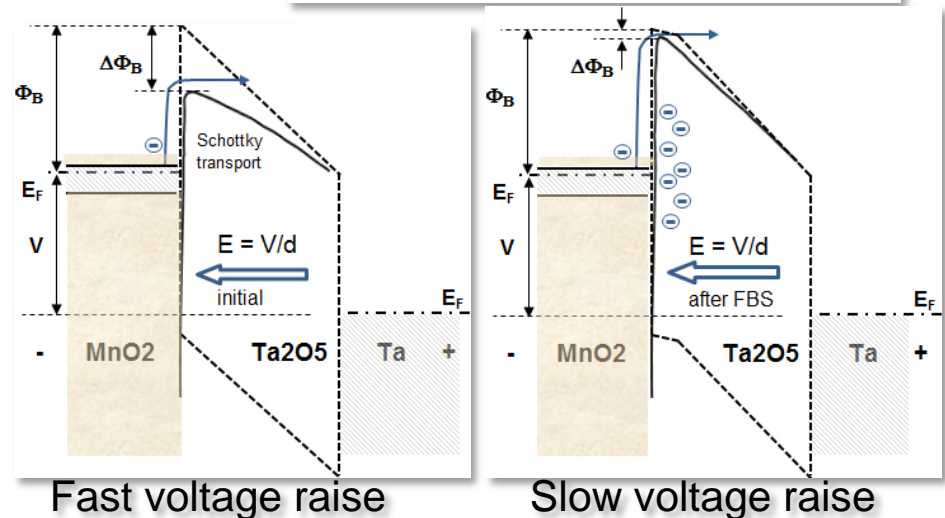
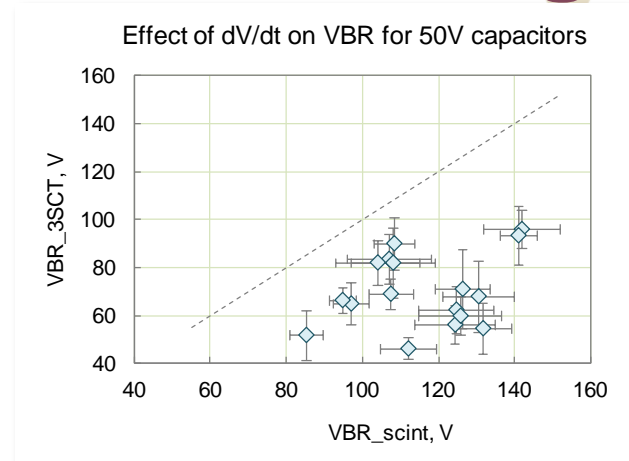


# Effect of $dV/dt$ on Breakdown Voltage

❑ Scintillation breakdown voltage,  $VBR_{scint}$  ( $dV/dt \sim 1$  to  $5$  V/sec) is always greater than the surge current breakdown voltage,  $VBR_{SCT}$  ( $dV/dt \sim 10^5$  to  $10^6$  V/sec)

❑ The rate of voltage increase changes charges and electrical field at the interface.

Accumulation of electrons on traps at the  $MnO_2-Ta_2O_5$  interface with time increases the barrier, the level of electron injection, and the probability of avalanching.



- ✓ A theory explains decreasing VBR with a rate of voltage increase.
- ✓ A resistor in series with a capacitor reduces  $dV/dt$  and failures.

# Requirements for Limiting Resistors

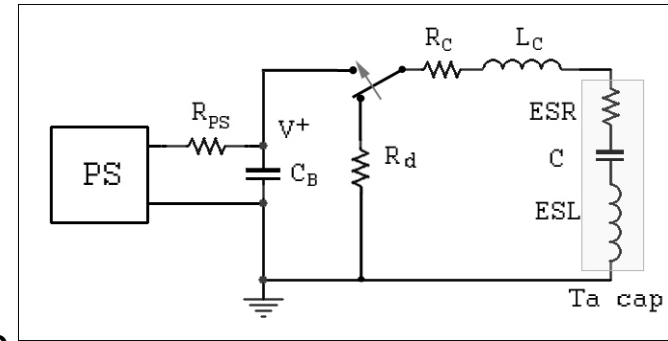
- ❑ History of requirements for circuit resistance ( $R_{ac}$ ):
    - In the 1960s: 3  $\Omega$  per each volt of operating voltage.
    - By the 1980s: 1  $\Omega$  per each volt.
    - From the 1990s: 0.1  $\Omega$  per volt or 1 ohm, whichever is greater.
  - ❑ Manufacturers consider surge current failures as the major reason for voltage derating.
  - ❑ Do we need derating of currents in addition to voltage?
  - ❑ The limit for acceptable surge currents is set by the SCT conditions: the current during applications should not exceed the current during testing:  $I_{appl.} < I_{test}$  “use as tested”
- ✓ Improvements in reliability and the need to increase the efficiency of power supply systems resulted in reduction of  $R_{ac}$ .
  - ✓ Can we allow circuit designs without  $R_{ac}$ ?
  - ✓ Need a closer look at how the  $I_{test}$  is specified.



# MIL-PRF 55365 Requirements

## ❑ SCT per MIL-PRF-55365H:

- $N_c = 4$  surge cycles.
- Energy storage capacitor,  $C_B = 20 \times C_{DUT}$
- Test voltage: VR
- Charge time,  $t_{ch}$ , and discharge time,  $t_{disch}$ ,  $\geq 1$  sec.
- Total DC resistance of the circuit,  $R_C$ , including the wiring, fixturing, and output impedance of the power supply should not exceed  $R_C = 1 \Omega$ .
- Measurements after SCT: DCL, C, DF (still no requirements for ESR)
- $I_{test} \geq \frac{V_R}{(R_{tc} + ESR_{spec})}$ , where resistance of the test circuit,  $R_{tc} = 1 \Omega$ .
- Failure condition:  $I = 1A$  after 1ms for  $C \leq 330\mu F$ ; 10ms for  $C \leq 3.3mF$ , and 100ms for  $C > 3.3 mF$ .



## ❑ Before 12/1/2012:

- $N_c = 10$ .
- $t_{disch} = t_{ch} = 4$  sec.
- $R_C \leq 1.2$  Ohms.
- $C_B \geq 50$  mF.
- $I_{test}$  was not addressed.

✓ New specification recognizes the role of ESR as a limiting factor for surge currents.

✓ Rated surge current:

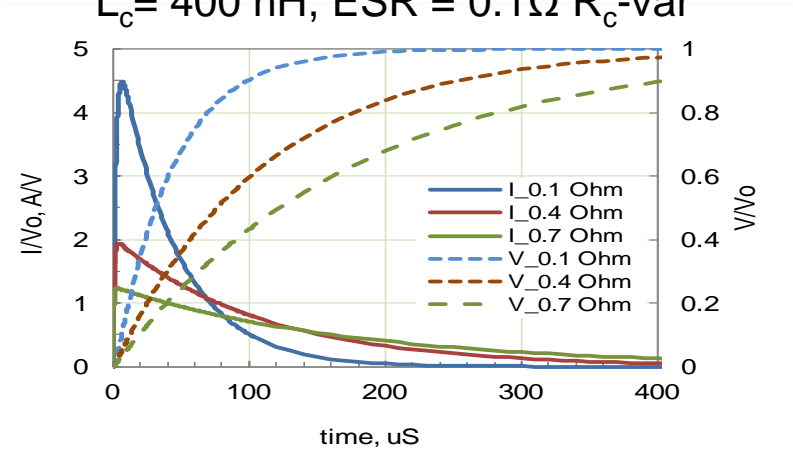
$$I_{surge} = \frac{V_R}{ESR_{spec} + 1}$$

✓ No specifics on  $I_{test}$  verification.

# Verification of SCT Conditions

- ❑ Two methods of SCT verification:
  - measurements of voltage after some time of spike initiation;
  - measurements of a current spike amplitude.

SCT simulations for 220  $\mu\text{F}$  capacitor at  $L_c = 400 \text{ nH}$ ,  $\text{ESR} = 0.1 \Omega$   $R_c$ -var

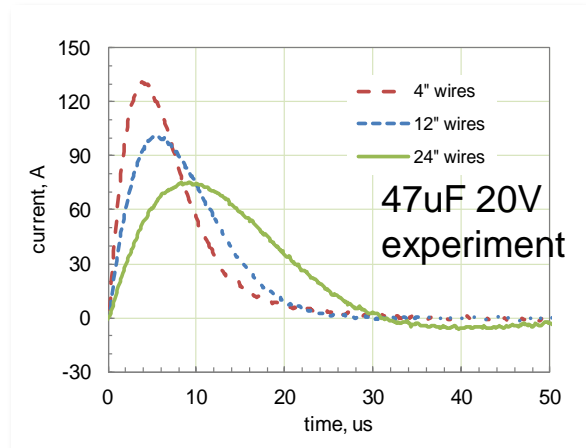


- ✓ The rate of voltage increase is critical for SCT.
- ✓ A high current spike is a byproduct of the fast voltage raise, rather than the major cause of failure.
- ✓ Even minor variations ( $\sim 0.1 \Omega$ ) of  $R_c$  affect  $dV/dt$  and results of SCT.
- ✓ The amplitude of the current spike is the most adequate characteristic of the SCT conditions.

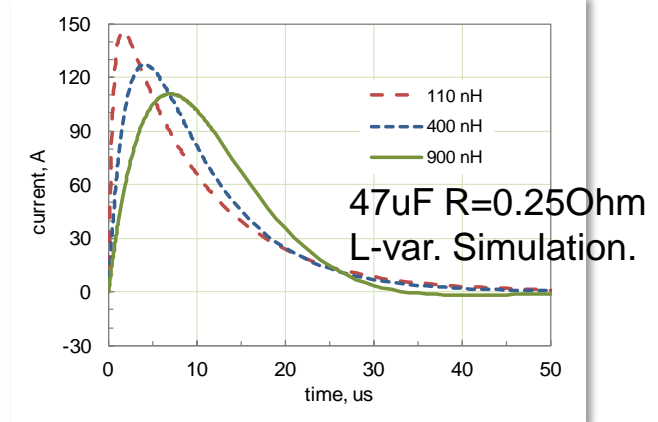
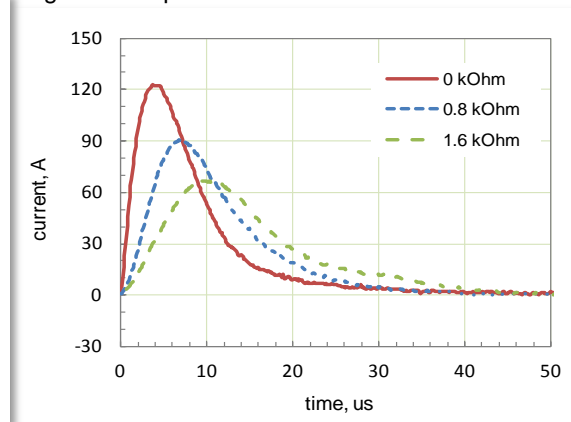
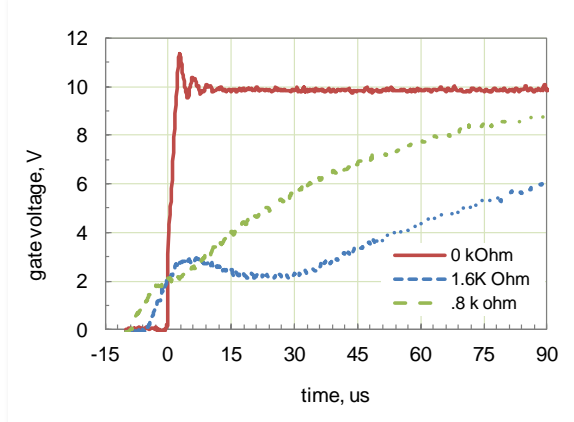
# Factors Affecting SCT Results

- ❑  $R_c$  includes resistance of wires and contacts.
- ❑ The length of wires affects inductance.
- ❑ Type of switch.
- ❑ The rate of voltage increase in case of FET.

Effect of wire length



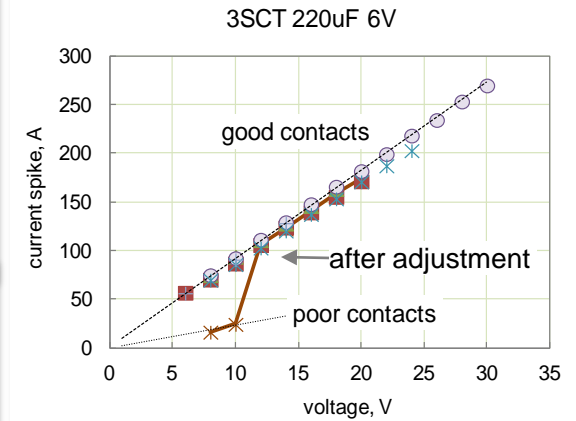
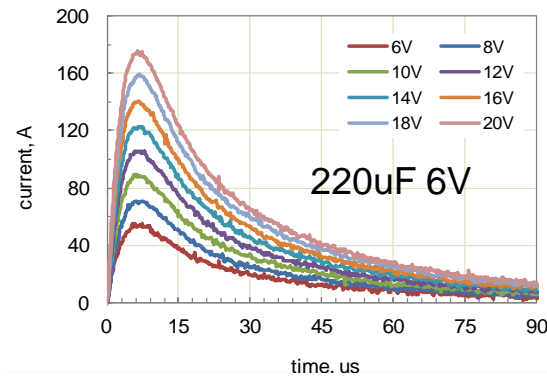
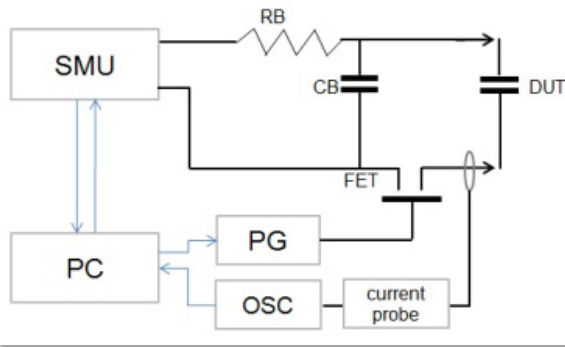
Effect of resistance to FET gate on  $V_g$  and  $I_{sp}$  for 47uF 20V capacitors



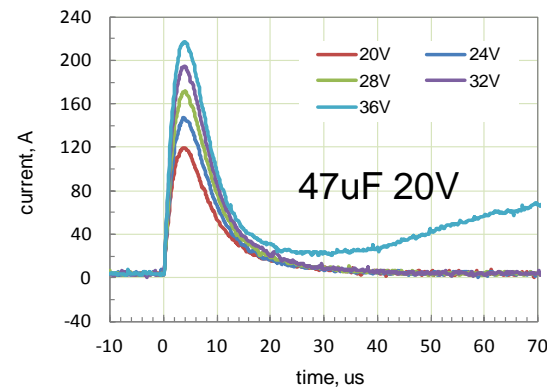
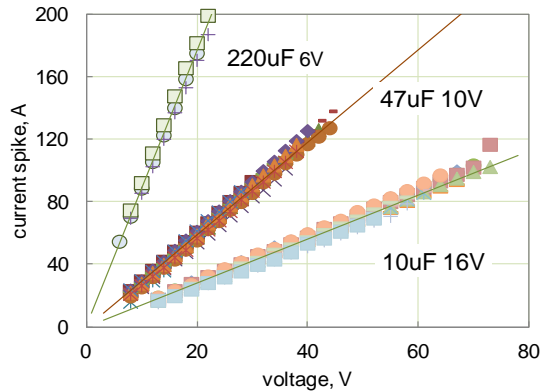
✓ SCT test conditions should be optimized by maximizing  $I_{sp}$ .



# Effective Resistance of the Circuit



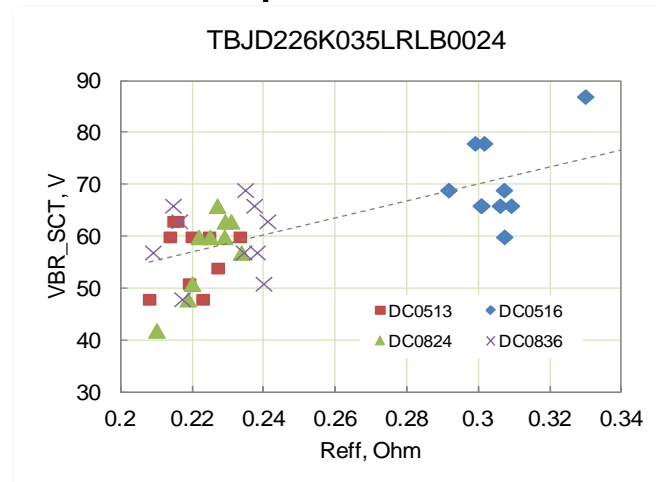
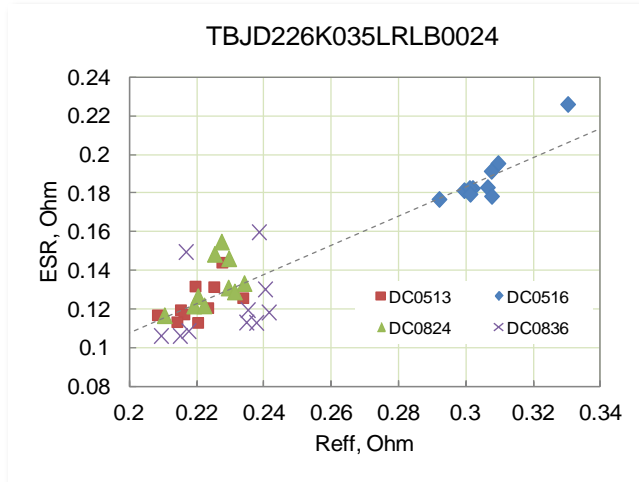
Test anomalies, e.g. poor contacts, can be revealed by  $I_{sp}(V)$  curves



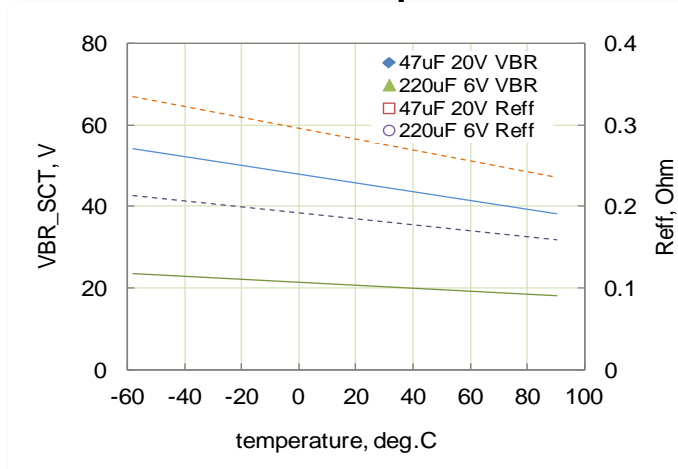
- ✓  $I_{sp}$  increases linearly with voltage allowing for calculations of the effective resistance of the circuit,  $R_{eff}$ .
- ✓  $R_{eff}$  corresponds to the impedance of the circuit and includes  $R_C$ ,  $ESR$ , resistance of contacts, and circuit inductance,  $L_C$ .

# Effect of $R_{eff}$ on Breakdown Voltage

□ Different lot date codes of 22  $\mu$ F 35V capacitors.

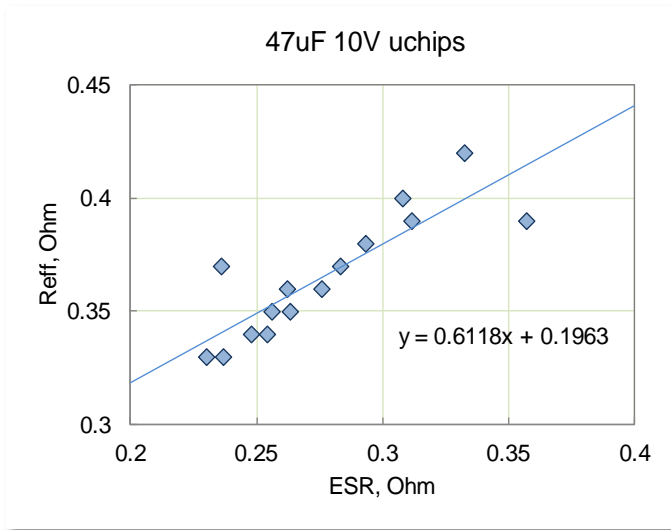


□ Effect of temperature

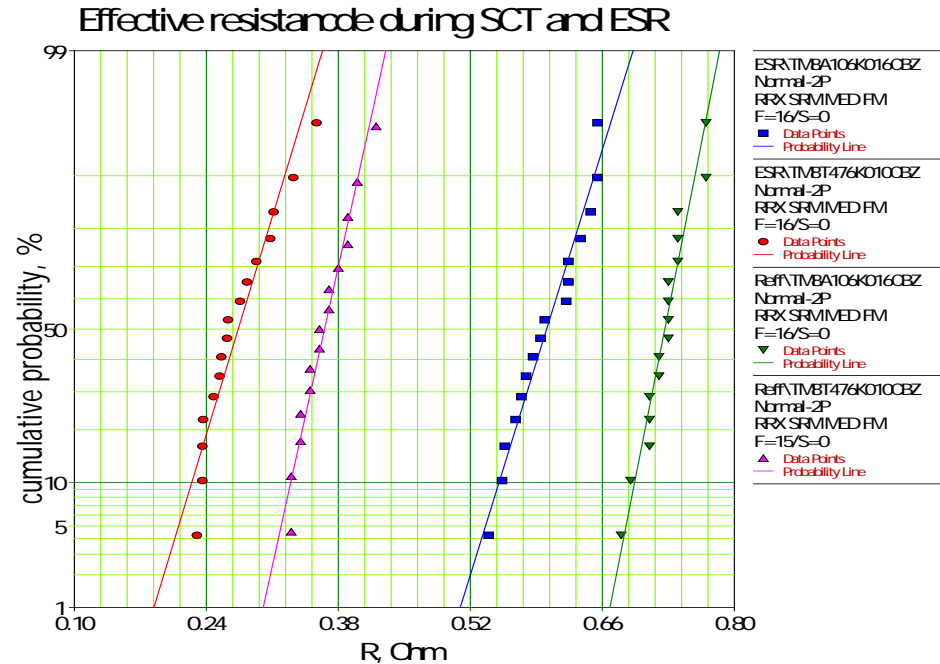
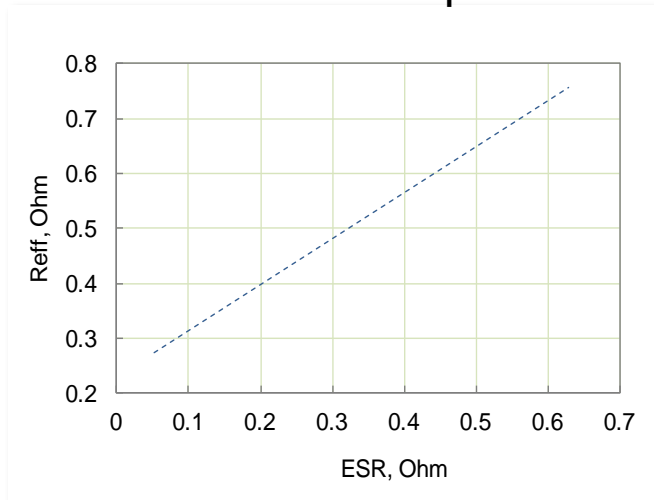


- ✓ Parts with larger *ESR* had greater VBR.
- ✓ Temperature decreases ESR resulting in lower VBR.
- ✓ An increase in  $R_{eff}$  by  $\sim 0.1\Omega$  results in increase of VBR  $\sim 10\%$ .

# Correlation between ESR and $R_{eff}$



20 lots of HV capacitors



✓ Effective resistance of SCT:

$$R_{eff} = \frac{V_R}{I_{sp}} \approx R_c + ESR$$

✓ Optimized set-up:  $R_c$  is in the range from 0.1  $\Omega$  to 0.2  $\Omega$ .

# Application vs. Test Conditions

## □ Typical application conditions:

- No limiting resistors, minimal inductance.
- No contact resistance.
- Resistance of the circuit,  $R_{ac}$ , is minimal.

➤ The current is limited mostly by ESR.

## □ Surge Current Test conditions:

- Contact resistance of fixtures.
- Limiting resistor (up to 1  $\Omega$ ).
- Relatively long wires and inductance.
- No requirements for  $I_{test}$  verification.

➤ Parts with poor contacts in the fixture can pass the testing.

## Example:

- A 15 $\mu$ F 10V CWR06 capacitor with specified ESR=2.5 $\Omega$  and real ESR = 0.5 $\Omega$  is used in a 5V line.
- During application the part can experience a spike:

$$\underline{I_{appl} = 5/0.5 = 10 \text{ A.}}$$

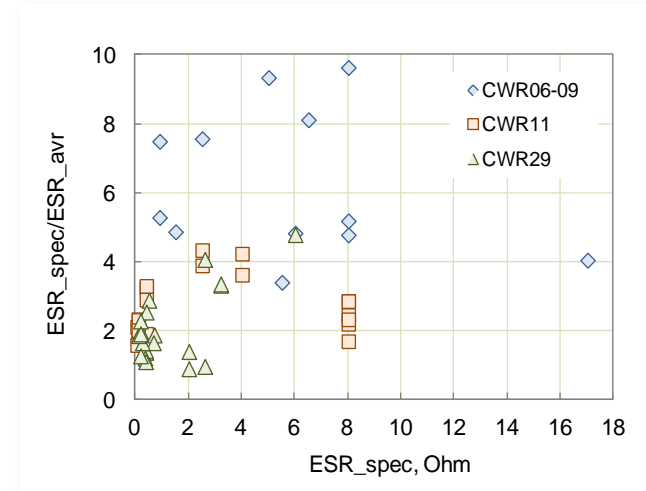
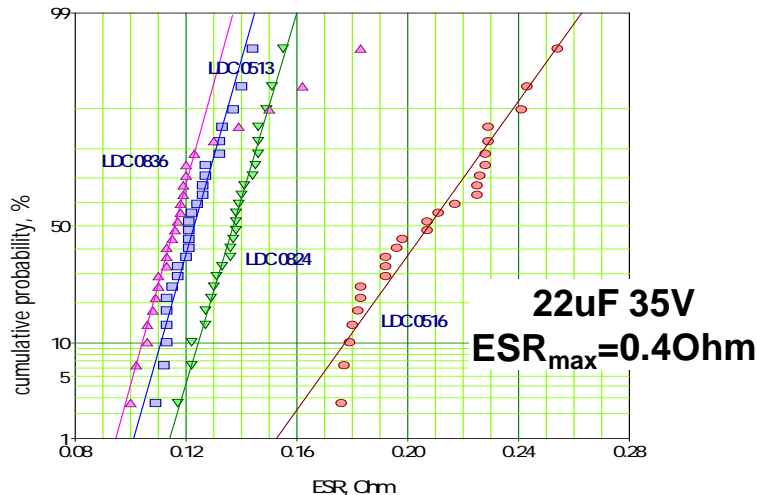
- During the testing it will be verified to the current:

$$I_{test} \geq V_R / (R_{tc} + ESR_{spec})$$

$$\underline{I_{test} = 10 / (1 + 2.5) = 2.8 \text{ A}}$$

✓ There might be a substantial difference in inrush currents between application and test conditions.

# Real and Specified Values of ESR



- ✓ ESR distribution can be described by a normal function.
- ✓ The distributions are rather tight: STD ~ 30% to 50% of ESR<sub>avr</sub>.
- ✓ Different lots of the same part type might have different ESR.
- ✓ Only a maximum value of ESR is limited. Real ESR values might not correlate with the limit.
- ✓  $N_{avr} = ESR_{limit} / ESR_{avr}$
- ✓ CWR06 have  $N_{avr} \sim 7$ , CWR29  $\sim 2$ .

	CWR06	CWR11	CWR29
$N_{avr}$	6.92	2.72	2.04
STD	2.64	0.83	1.02
Lots QTY	14	20	23

# Surge Current Derating

- ❑ SCT requirements (rated current):  $I_{test} = \frac{V_R}{R_{test} + ESR_{spec}}$ ,  
 $R_{test} = 1 \Omega$ .

- ❑ During applications, possible current spike:  $I_a = \frac{\alpha \times V_R}{R_{ac} + ESR}$ ,  
 derating  $\alpha = V_a/V_R$ ,  $R_{ac}$  – additional resistance

- ❑ Derating Criterion:  $I_a < \beta \times I_{test}$ , where  $\beta \leq 1$  is the current derating coefficient.

- ❑ Substitution gives:  $R_{ac} > \frac{\alpha}{\beta} \times R_{test} + \frac{\alpha}{\beta} \times ESR_{spec} - ESR$

- ❑ At low voltages capacitors can tolerate much higher current spikes, so there is no need in derating currents on the top of voltage derating =>  $R_{ac} > \alpha \times R_{test} + \alpha \times ESR_{spec} - ESR$

✓  $R_{ac}$  is not necessary if  $I_{ps\_max} < I_{test}$  at a clamping time  $\tau \leq 10 \mu s$ .

✓ Unless SCT is done at the optimized conditions, or  $\alpha < \frac{ESR}{ESR_{spec} + R_{test}}$  additional resistance is necessary.



# When Additional Resistor is Necessary?

- ❑ If SCT is carried out at the optimized conditions ( $R_{tc} < 0.5 \Omega$ , and  $I_{sp}$  is verified at real ESR values), then

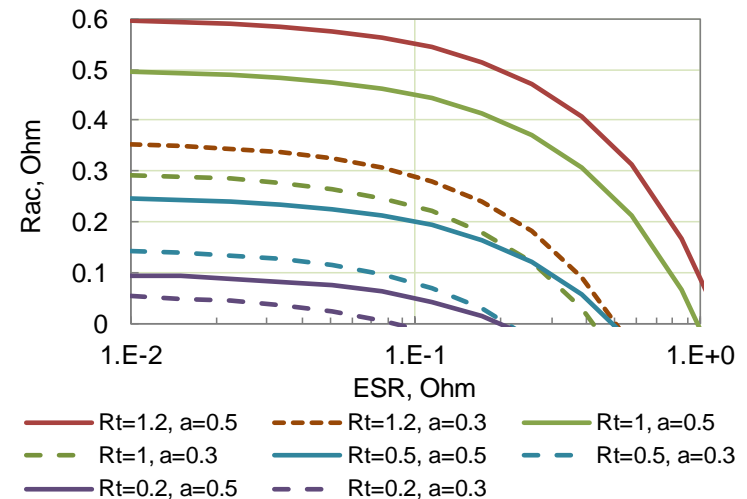
$$R_{ac} > \alpha \times R_{tc} + (\alpha - 1) \times ESR$$

- ❑ If  $R_{ac} < 0.05 \Omega$ , no resistance required.

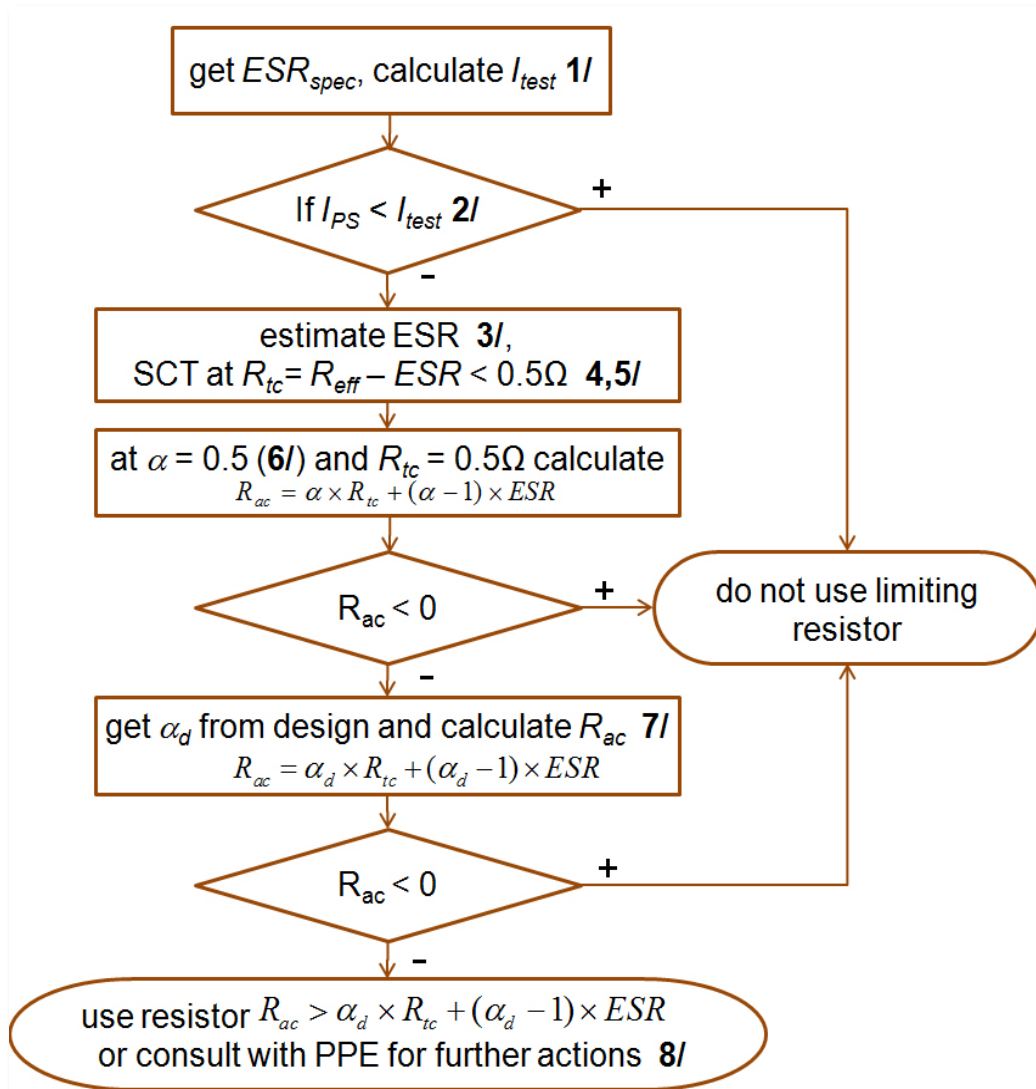
- ✓ At the existing SCT requirements per M55365, additional resistance is necessary in most cases.
- ✓ If SCT is carried out at  $R_{tc} = R_{eff} - ESR < 0.5 \Omega$ , the additional resistor is not necessary if

$$(1 - \alpha) \times ESR > \alpha \times R_{tc}$$

Required series resistance at different ESR,  $R_{tc}$  and  $\alpha$



# Algorithm for Surge Current Derating



1/  $I_{test} = \frac{V_R}{R_{tc} + ESR_{spec}}$ ,  $R_{tc} = 1 \Omega$

2/ In case of using power supplies (PS) with current compliance, make sure that the clamping time  $\tau \leq 10\mu s$ .  $I_{PS} = I_{max} PS$ .

3/ Estimate ESR as  $ESR_{spec}/N$ , where  $N=7, 3, 2$  for CWR06/11/29 respectively.

4/  $R_{eff} = V_R/I_{sp}$ , where  $I_{sp}$  is the surge current spike amplitude.

5/ SCT should be carried out at a min. wire length, no limiting resistors, and  $I_{sp}$  should be verified to be greater than  $I_{sp} > V_R/(0.5 + ESR)$

6/ Standard voltage derating:  $\alpha = 0.5$

7/ Actual derating:  $\alpha_d = V_{app}/V_R$

8/ Suggestions for further actions:

- experimental data for ESR,
- calculate actual  $R_{tc} = R_{eff} - ESR$ ,
- SCT at greater voltage levels, ...

# Conclusion

- ❑ Tantalum capacitors manufactured per MIL-PRF-55365 might fail because the surge current test conditions during manufacturing are less stressful compared to application conditions.
- ❑ Measurements of current spike amplitudes during SCT allow for estimations of the effective resistance of the test circuit,  $R_{eff}$ , and should be used to assure that the parts are properly stressed during the testing. Acceptable test conditions can be determined as  $R_{eff} \leq 0.5 + ESR$ .
- ❑ An algorithm and procedures necessary for selection of limiting resistors to derate surge currents or for making a decision to use tantalum capacitors without additional resistors are suggested.